

**FEATURES**

- Red to Near Infrared Enhanced Photodiode
- Photosensitive Active Area: 1 mm x 1 mm
- High Sensitivity: 0.62 A/W ( $\lambda = 850$  nm), 0.35 A/W ( $\lambda = 1064$  nm)
- Wide Operating Temperature: -40°C to +125°C
- Ideal for Laser Monitoring Applications
- RoHS and REACH Compliant

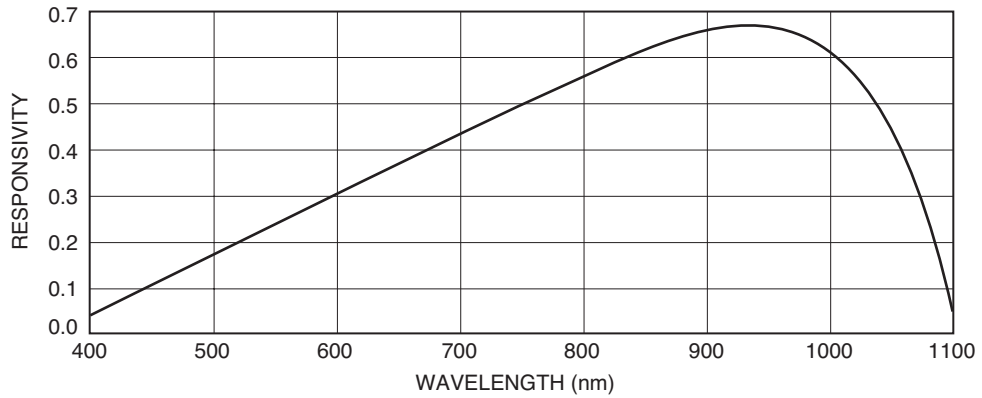
**Electro-Optical Characteristics at 25°C**

Parameters	Test Conditions	Min	Typ	Max	Units
Active Area			1		mm <sup>2</sup>
Spectral Response Range, $\lambda$		320		1100	nm
Responsivity	@ 850 nm		0.62		A/W
Responsivity	@ 1064 nm		0.35		A/W
Dark Current, $I_{dr}$	$V_r = 3$ V		0.1	0.75	nA
Shunt Resistance	$V_R = 10$ mV	200	500		M $\Omega$
Reverse Breakdown Voltage, $V_R$	$I_R = 1$ $\mu$ A	50			Volts
Capacitance, C	$V_R = 0$ V		3		pF
Rise Time	$V_R = 5$ V		50		nsec

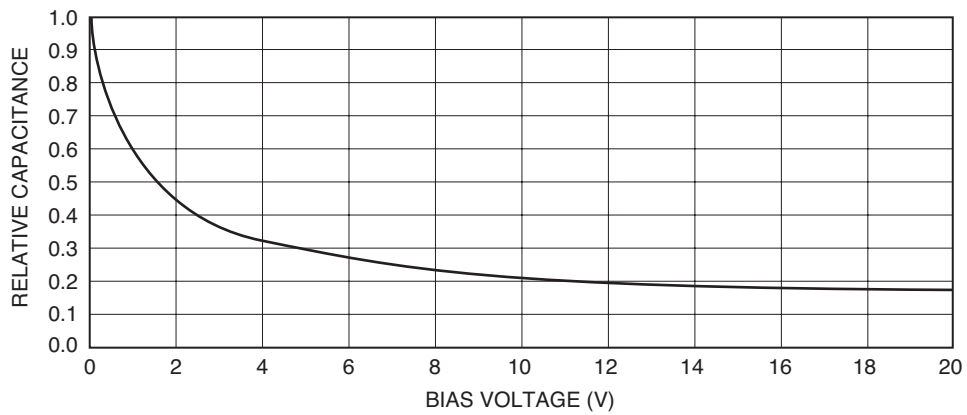
**Thermal Parameters**

Parameters	Units
Storage and Operating Temperature Range	-40°C to 125°C
Maximum Junction Temperature	125°C

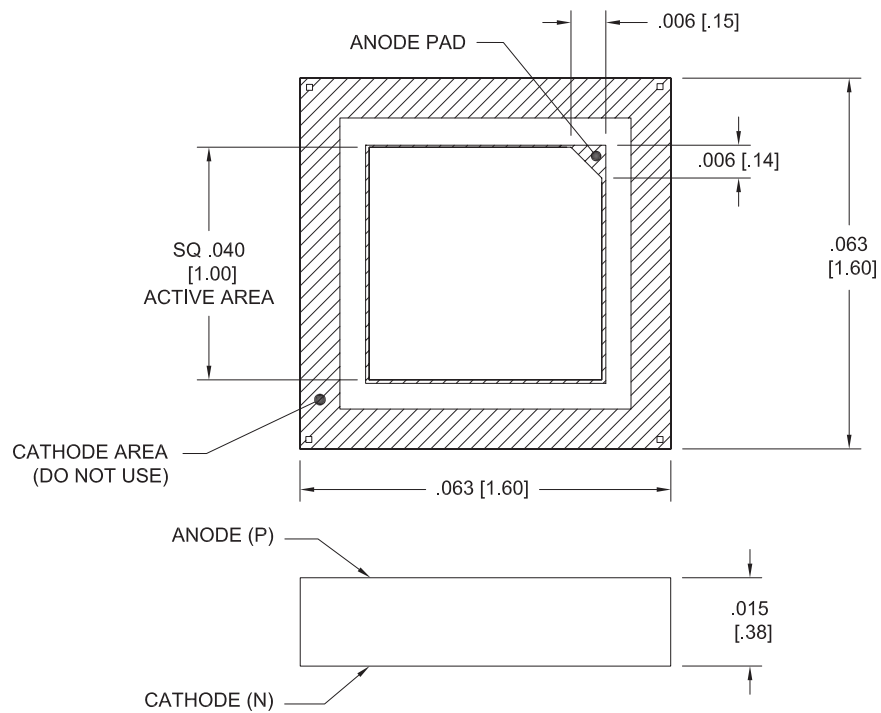
**Typical Spectral Response**



**Capacitance vs Bias Voltage**



**Package Dimensions**



Specifications are subject to change without prior notice.